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27

26

25

2D7

2D8

2LE

2Q7 🛛

2Q8

2<mark>0</mark>E

22

23

24

● Members of the Texas Instruments <i>Widebus</i> ™ Family	SN54ABT16373A WD PACKAGE SN74ABT16373A DGG OR DL PACKAGE (TOP VIEW)
<ul> <li>State-of-the-Art EPIC-IIB<sup>™</sup> BiCMOS Design Significantly Reduces Power Dissipation</li> </ul>	
<ul> <li>Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17</li> </ul>	1Q1 [ 2 47 ] 1D1 1Q2 [ 3 46 ] 1D2
<ul> <li>Typical V<sub>OLP</sub> (Output Ground Bounce)</li> <li>&lt; 0.8 V at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C</li> </ul>	GND
<ul> <li>High-Impedance State During Power Up and Power Down</li> </ul>	$1Q4\begin{bmatrix}6 & 43\end{bmatrix}1D4$ $V_{CC}\begin{bmatrix}7 & 42\end{bmatrix}V_{CC}$
<ul> <li>Distributed V<sub>CC</sub> and GND Pin Configuration Minimizes High-Speed Switching Noise</li> </ul>	1Q5 [] 8 41 [] 1D5 1Q6 [] 9 40 [] 1D6 GND [] 10 39 [] GND
<ul> <li>Flow-Through Architecture Optimizes PCB Layout</li> </ul>	1Q7 [ 11 38 ] 1D7 1Q8 [ 12 37 ] 1D8
<ul> <li>High-Drive Outputs (–32-mA I<sub>OH</sub>, 64-mA I<sub>OL</sub>)</li> </ul>	2Q1 🛛 13 36 🗍 2D1
<ul> <li>Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink</li> </ul>	2Q2
Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package	2Q3 [ <sub>16</sub> <sub>33</sub> ] 2D3 2Q4 [ <sub>17</sub> <sub>32</sub> ] 2D4
Using 25-mil Center-to-Center Spacings	V <sub>CC</sub>
description	2Q6 🛛 <sub>20 29</sub> 🕽 2D6
The 'ADT10272A are 10 hit transported D time	GND 21 28 GND

The 'ABT16373A are 16-bit transparent D-type latches with 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ( $\overline{OE}$ ) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

OE does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

When  $V_{CC}$  is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, OE should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ABT16373A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT16373A is characterized for operation from -40°C to 85°C.



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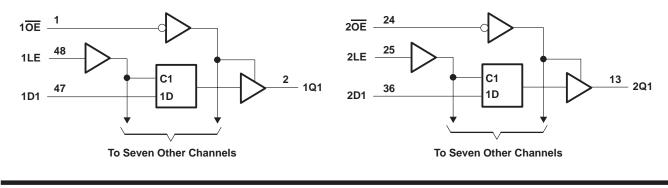
#### **FUNCTION TABLE** (each 8-bit section) INPUTS OUTPUT Q OE LE D L Н Н Н L н L L L Х L $Q_0$ Н Х Х Ζ

#### logic symbol<sup>†</sup>

			_	
1 <mark>0E</mark>	1	1EN		
1LE	48	C3		
20E	24	2EN		
	25			
2LE		C4		
1D1	47	3D 1 ▽	2	1Q1
1D2	46		3	1Q2
1D3	44	-	5	1Q3
1D4	43		6	1Q4
1D5	41	-	8	1Q5
1D6	40	-	9	1Q6
1D7	38	-	11	1Q7
1D8	37	-	12	1Q8
2D1	36	4D 2 ⊽	13	2Q1
2D2	35		14	2Q2
2D3	33		16	2Q3
2D4	32		17	2Q4
2D5	30		19	2Q5
2D6	29		20	2Q6
2D7	27		22	2Q7
2D8	26		23	2Q8
			J	

<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

### logic diagram (positive logic)





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#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub> Input voltage range, V <sub>I</sub> (see Note 1)	
Voltage range applied to any output in the high or power-off state, Vo	–0.5 V to 5.5 V
Current into any output in the low state, Io: SN54ABT16373A	96 mA
SN74ABT16373A	128 mA
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–18 mA
Output clamp current, $I_{OK}$ (V <sub>O</sub> < 0)	–50 mA
Package thermal impedance, $\theta_{JA}$ (see Note 2): DGG package	
DL package	
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

#### recommended operating conditions (see Note 3)

				16373A	SN74ABT1	16373A	UNIT
			MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage		4.5	5.5	4.5	5.5	V
VIH	High-level input voltage		2		2		V
VIL	Low-level input voltage			0.8		0.8	V
VI	Input voltage		0	VCC	0	VCC	V
ЮН	High-level output current			-24		-32	mA
IOL	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate	ramp rate			200		μs/V
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.



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#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST OO	Т	A = 25°0	;	SN54ABT	16373A	SN74ABT1	16373A	UNIT		
		TEST CONDITIONS		MIN	TYP <sup>†</sup>	MAX	MIN	MAX	MIN	MAX	UNIT	
VIK		V <sub>CC</sub> = 4.5 V,	lj = -18 mA			-1.2		-1.2		-1.2	V	
		V <sub>CC</sub> = 4.5 V,	I <sub>OH</sub> = -3 mA	2.5			2.5		2.5			
Vari		V <sub>CC</sub> = 5 V,	I <sub>OH</sub> = -3 mA	3			3		3		v	
VOH		V <sub>CC</sub> = 4.5 V	I <sub>OH</sub> = -24 mA	2			2				V	
		VCC = 4.3 V	$I_{OH} = -32 \text{ mA}$	2*					2			
VOL		V <sub>CC</sub> = 4.5 V	I <sub>OL</sub> = 48 mA			0.55		0.55			V	
VOL		VCC = 4.3 V	I <sub>OL</sub> = 64 mA			0.55*				0.55	v	
V <sub>hys</sub>					100						mV	
II.		$V_{CC} = 0$ to 5.5 V V <sub>I</sub> = V <sub>CC</sub> or GN				±1		±1		±1	μΑ	
IOZPU	‡ر	$V_{CC} = 0 \text{ to } 2.1 \text{ V}$ $V_{O} = 0.5 \text{ V to } 2.1 \text{ V}$	V, 7 V, <del>OE</del> = X			±50		±50		±50	μA	
IOZPE	) <sup>‡</sup>	$V_{CC} = 2.1 V to$ $V_{O} = 0.5 V to 2.000 V_{O}$	0, 7 V, <del>OE</del> = X			±50		±50		±50	μA	
IOZH		$V_{CC} = 2.1 \text{ V} \text{ to}$ $V_{O} = 2.7 \text{ V}, \overline{\text{OE}}$				10		10		10	μΑ	
I <sub>OZL</sub>		$V_{CC} = 2.1 \text{ V} \text{ to}$ $V_{O} = 0.5 \text{ V}, \overline{\text{OE}}$				-10		-10		-10	μΑ	
l <sub>off</sub>		$V_{CC} = 0, V_{I} \text{ or } V_{I}$	/ <sub>O</sub> ≤ 4.5 V			±100				±100	μΑ	
ICEX	Outputs high	V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 5.5 V			50		50		50	μΑ	
ΙΟ§		V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 2.5 V	-50	-100	-180	-50	-180	-50	-180	mA	
	Outputs high					2		2		2		
ICC	Outputs low	V <sub>CC</sub> = 5.5 V, I <sub>O</sub> V <sub>I</sub> = V <sub>CC</sub> or GN				85		85		85	85 mA	
	Outputs disabled					2		2		2		
∆ICC	T	V <sub>CC</sub> = 5.5 V, Or Other inputs at V	ne input at 3.4 V, √ <sub>CC</sub> or GND			1.5		1.5		1.5	mA	
Ci		V <sub>I</sub> = 2.5 V or 0.5	5 V		3.5						pF	
Co		V <sub>O</sub> = 2.5 V or 0.	.5 V		9.5						рF	

\* On products compliant to MIL-PRF-38535, this parameter does not apply.

<sup>†</sup> All typical values are at  $V_{CC} = 5$  V.

<sup>‡</sup> This parameter is characterized, but not production tested.

§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

 $\P$  This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.

#### timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

		V <sub>CC</sub> = 5 V, T <sub>A</sub> = 25°C <sup>#</sup>		SN54ABT1	16373A	SN74ABT1	16373A	UNIT
			MAX	MIN	MAX	MIN	MAX	
tw	Pulse duration, LE high	3.3		3.3		3.3		ns
t <sub>su</sub>	Setup time, data before LE $\downarrow$	1.5		2.4		1.5		ns
t <sub>h</sub>	Hold time, data after LE $\downarrow$	1		2.2		1		ns

<sup>#</sup> These values apply only to the SN74ABT16373A.



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# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

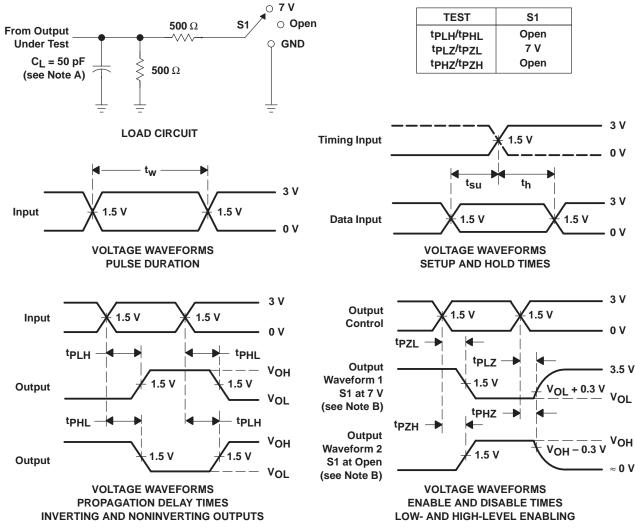
			SN54	ABT163	73A			
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V( Tj	CC = 5 V A = 25°C	l, ;	MIN	МАХ	UNIT
			MIN	TYP	MAX			
<sup>t</sup> PLH	D	Q	1.4	3.7	5.3	1.4	6.5	ns
<sup>t</sup> PHL		Q	2	4	5.4	2	6.5	115
<sup>t</sup> PLH	LE	Q	1.7	4.1	5.7	1.7	7	ns
<sup>t</sup> PHL		Q	2.3	4.3	5.6	2.3	6.3	115
<sup>t</sup> PZH	ŌĒ	Q	1.1	3.4	5	1.1	6.4	ns
<sup>t</sup> PZL		Q	1.5	3.5	4.9	1.5	5.8	115
<sup>t</sup> PHZ	OE	Q	2.4	5.1	7.1	2.4	8.3	ns
<sup>t</sup> PLZ	UE	Q	1.6	4.4	6.3	1.6	8	115

switching characteristics over recommended ranges of supply voltage and operating free-air temperature,  $C_L = 50 \text{ pF}$  (unless otherwise noted) (see Figure 1)

				SN74	ABT163	573A		
PARAMETER	FROM (INPUT)	TO (OUTPUT)	Vo Тį	V <sub>CC</sub> = 5 V, T <sub>A</sub> = 25°C			МАХ	UNIT
			MIN	TYP	MAX			
tPLH	D	Q	1.4	3.7	5.3	1.4	6.3	ns
<sup>t</sup> PHL		Q	2	4	5.4	2	6.2	115
<sup>t</sup> PLH	LE	Q	1.7	4.1	5.7	1.7	6.7	ns
<sup>t</sup> PHL		Q	2.3	4.3	5.6	2.3	6.1	115
<sup>t</sup> PZH	OE	Q	1.1	3.4	5	1.1	6.1	ns
<sup>t</sup> PZL	ÛE	4	1.5	3.5	4.9	1.5	5.6	115
<sup>t</sup> PHZ	OE	Q	2.4	5.1	7.1	2.4	8.1	ns
tPLZ	UE	Q	1.6	4.4	5.8	1.6	6.5	115



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#### PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.

D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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